

Title (en)
METHOD FOR PRODUCING Laterally Isolated SILICIUM AREAS

Publication
EP 0000897 B1 19811223 (DE)

Application
EP 78100614 A 19780807

Priority
US 82436177 A 19770815

Abstract (en)
[origin: US4104086A] A method for isolating regions of silicon involving the formation of openings that have a suitable taper in a block of silicon, thermally oxidizing the surfaces of the openings, and filling the openings with a dielectric material to isolate regions of silicon within the silicon block. The method is particularly useful wherein the openings are made through a region of silicon having a layer of a high doping conductivity.

IPC 1-7
H01L 21/76; **H01L 21/263**

IPC 8 full level
H01L 21/3065 (2006.01); **H01L 21/308** (2006.01); **H01L 21/76** (2006.01); **H01L 21/762** (2006.01)

CPC (source: EP US)
H01L 21/3065 (2013.01 - EP US); **H01L 21/3081** (2013.01 - EP US); **H01L 21/76232** (2013.01 - EP US); **Y10S 148/051** (2013.01 - EP US); **Y10S 148/131** (2013.01 - EP US); **Y10S 148/161** (2013.01 - EP US); **Y10S 148/168** (2013.01 - EP US); **Y10S 438/978** (2013.01 - EP US)

Cited by
EP0005728A1; EP0048175A3

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
US 4104086 A 19780801; CA 1097826 A 19810317; DE 2861453 D1 19820211; EP 0000897 A1 19790307; EP 0000897 B1 19811223; IT 1112298 B 19860113; IT 7826393 A0 19780802; JP S5432277 A 19790309; JP S6220696 B2 19870508

DOCDB simple family (application)
US 82436177 A 19770815; CA 305231 A 19780612; DE 2861453 T 19780807; EP 78100614 A 19780807; IT 2639378 A 19780802; JP 8217778 A 19780707